

Coloured-noise-induced transitions in nonlinear structures

Mankin, Romi; Laas, Tõnu; Soika, Erkki; **Sauga, Aho**; Rekker, Astrid; Ainsaar, Ain; Ugaste, Ülo Nukleonika 2008 / 3, p. 127-134 : ill
<https://bibliotekanauki.pl/articles/147752>

Gümnaasiumi füüsika ainekava ja riigieksam

Mere, Arvo; Ugaste, Ülo Konverentsi "Reaalained ja uus õppekava" materjalid : Tartu, 27.-28. oktoober 2000 2000 / lk. 82-87 : ill

Hydrogen interaction with point defects in the Si-SiO₂ structures and its influence on the interface properties

Kropman, Daniel; Mellikov, Enn; Kärner, T.; Ugaste, Ülo; Laas, Tõnu; Heinmaa, I.; Abru, Uno; Medvid, A. Solid state phenomena 2008 / p. 345-350 <https://www.scientific.net/SSP.131-133.345>

Impurity interaction with point defects in the Si-SiO₂ structures and its influence on the interface properties

Kropman, Daniel; Mellikov, Enn; Kärner, T.; Ugaste, Ülo; Laas, Tõnu; Heinmaa, I.; Medvid, A. Materials science and engineering : B 2006 / p. 222-226 : ill <https://www.sciencedirect.com/science/article/pii/S0921510706004375>

Interaction between point defects in the Si-SiO₂ system during the process of its formation

Kropman, Daniel; Kärner, T.; Samoson, Ago; Heidmaa, I.; Ugaste, Ülo; **Mellikov, Enn** Defect and Diffusion Forum 2001 / p. 1737-1744 <https://www.sciencedirect.com/science/article/abs/pii/S0168583X0100862X>

Interaction between point defects, extended defects and impurities in the Si-SiO₂ system during the process of its formation

Kropman, Daniel; Kärner, T.; Abru, Uno; Ugaste, Ülo; **Mellikov, Enn** Thin solid films 2004 / 1/2, p. 53-57 : ill
<https://www.sciencedirect.com/science/article/abs/pii/S0921510704003459>

Interaction between point defects, extended defects and impurities in the Si-SiO₂ system during the process of its formation

Kropman, Daniel; Kärner, T.; Abru, Uno; Ugaste, Ülo; **Mellikov, Enn; Kauk, Marit** Materials science and engineering : B 2004 / p. 295-298 : ill <https://www.sciencedirect.com/science/article/abs/pii/S0921510704003459>

Investigation of strain relaxation mechanism in Si-SiO₂ system during the process of its formation

Kropman, Daniel; Poll, V.; Kärner, T.; Ugaste, Ülo; **Mellikov, Enn**; Arbu, Uno; Paomets, V. Physica status solidi (a) 2003 / 2, p. 297-301 <https://onlinelibrary.wiley.com/doi/abs/10.1002/pssa.200306611>

Point defects interaction with extended defects and impurities and its influence on the Si-SiO₂ system properties

Kropman, Daniel; Arbu, Uno; Kärner, T.; Ugaste, Ülo; **Mellikov, Enn; Kauk, Marit**; Heinmaa, I.; **Samoson, Ago**; Medvid, A. Gettering and defect engineering in semiconductor technology. XI 2005 / p. 333-338 : ill
https://www.researchgate.net/publication/243760197_Point_Defects_Interaction_with_Extended_Defects_and_Impurities_and_Its_Influence_on_the_Si-SiO_2_System_Properties

Point defects interaction with extended defects in the Si-SiO₂ system [Electronic resource]

Kropman, Daniel; Kärner, T.; Abru, Uno; Ugaste, Ülo; **Mellikov, Enn** Proceedings IVC-16 : Venice, 2004 2004 / p. SS1-TuP394 [CD-ROM]
https://www.researchgate.net/publication/243760197_Point_Defects_Interaction_with_Extended_Defects_and_Impurities_and_Its_Influence_on_the_Si-SiO_2_System_Properties